

## Features

- Trench Power LV MOSFET Technology
- Excellent Package For Heat Dissipation
- High Density Cell Design For Low  $R_{DS(on)}$
- Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## Maximum Ratings

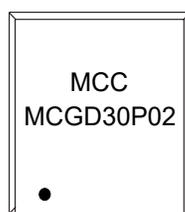
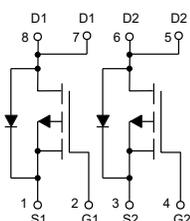
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 70°C/W Junction to Ambient (Note 2)
- Thermal Resistance: 5.9°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	±10	V
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	-30
		$T_A=100^\circ\text{C}$	-19
Pulsed Drain Current (Note 3)	$I_{DM}$	-120	A
Total Power Dissipation (Note 4)	$P_D$	21	W
Single Pulsed Avalanche Energy (Note 5)	$E_{AS}$	31	mJ

Note:

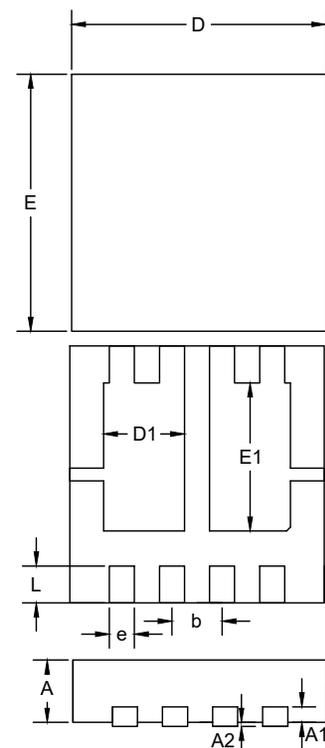
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ .
3. Repetitive rating; pulse width limited by max. junction temperature.
4.  $P_D$  is based on max. junction temperature, using junction-case thermal resistance.
5.  $T_J=25^\circ\text{C}$ ,  $V_{DD}=-20\text{V}$ ,  $V_G=-5\text{V}$ ,  $L=0.5\text{mH}$ .

## Internal Structure and Marking Code



# Dual P-CHANNEL MOSFET

## DFN3333-D



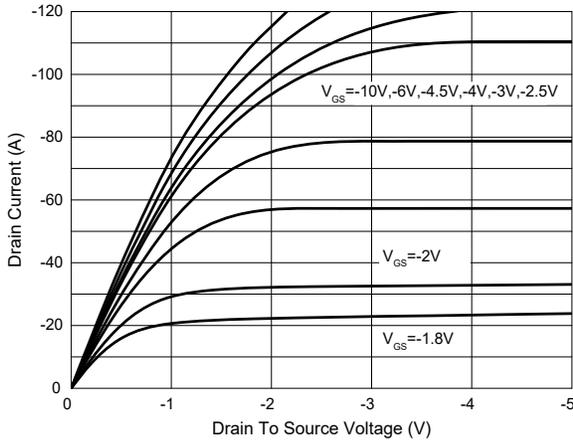
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.030	0.033	0.750	0.850	
A1	0.008		0.200		TYP
A2	-	0.002	-	0.050	
D	0.128	0.132	3.250	3.350	
E	0.128	0.132	3.250	3.350	
D1	0.039	0.043	1.000	1.100	
E1	0.073	0.077	1.850	1.950	
b	0.026		0.650		BSC
e	0.012	0.014	0.300	0.350	
L	0.017	0.021	0.425	0.525	

**Electrical Characteristics @ 25°C (Unless Otherwise Specified)**

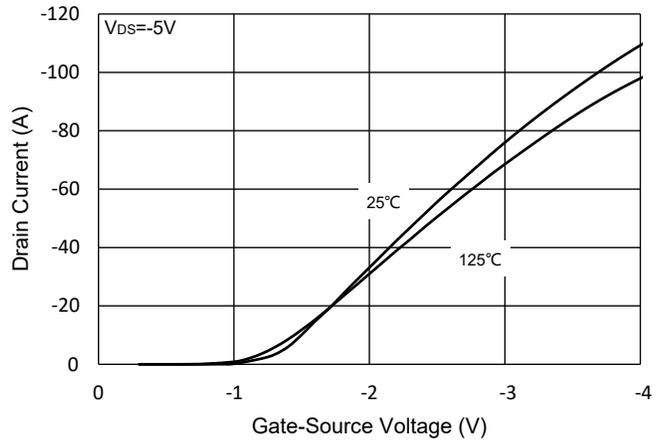
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 10V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$			-1	$\mu A$
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.62	-1.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-15A$		14	19	m $\Omega$
		$V_{GS}=-2.5V, I_D=-8A$		17	22	
		$V_{GS}=-1.8V, I_D=-6A$		22	30	
Gate Resisitance	$R_g$	f=1MHz, Open drain		13		$\Omega$
<b>Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$				-30	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=-30A$		-0.8	-1.2	V
Reverse Recovery Time	$t_{rr}$	$I_S=-6A, di/dt=100A/\mu s$		100		ns
Reverse Recovery Charge	$Q_{rr}$			146		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$		2157		pF
Output Capacitance	$C_{oss}$			285		
Reverse Transfer Capacitance	$C_{rss}$			255		
Total Gate Charge	$Q_g$	$V_{DS}=-15V, V_{GS}=-10V, I_D=-9.1A$		53.8		nC
Gate-Source Charge	$Q_{gs}$			2.8		
Gate-Drain Charge	$Q_{gd}$			7.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-15V, V_{GS}=-10V, R_G=2.5\Omega, I_D=-6A$		5.7		ns
Turn-On Rise Time	$t_r$			4		
Turn-Off Delay Time	$t_{d(off)}$			270		
Turn-Off Fall Time	$t_f$			100		

**Curve Characteristics**

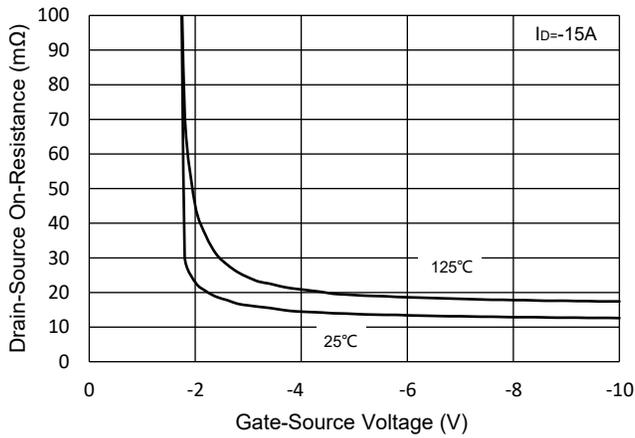
**Fig. 1 - Typical Output Characteristics**



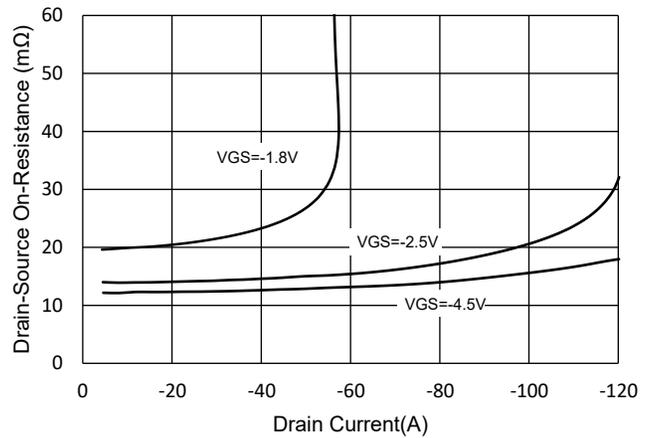
**Fig.2 Transfer Characteristic**



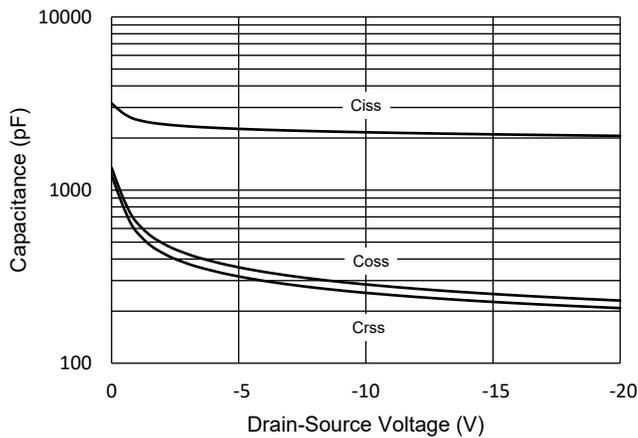
**Fig.3 Rds(ON)-Vgs**



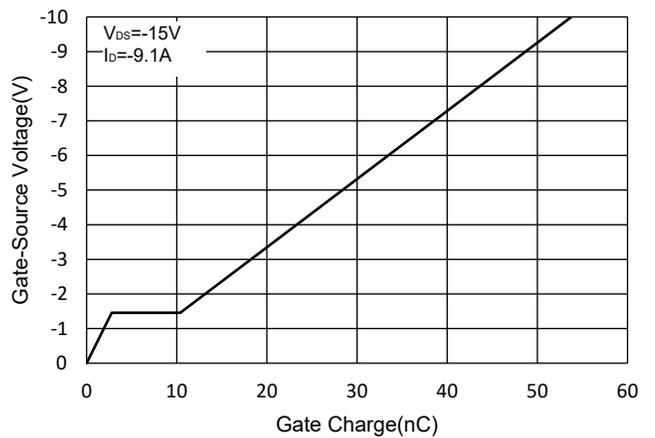
**Fig.4 Rds(ON)-Id**



**Fig.5 Capacitance Characteristics**

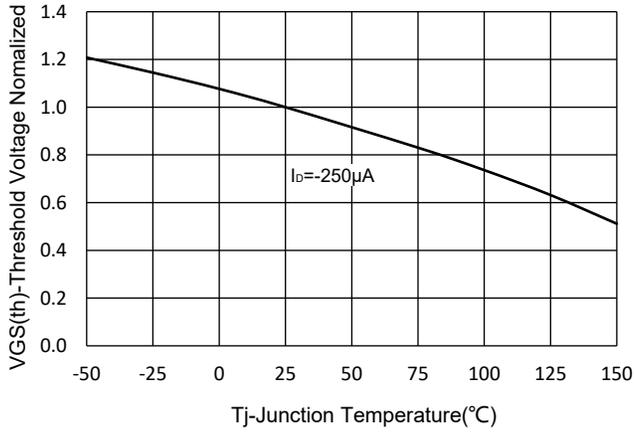


**Fig.6 Gate Charge**

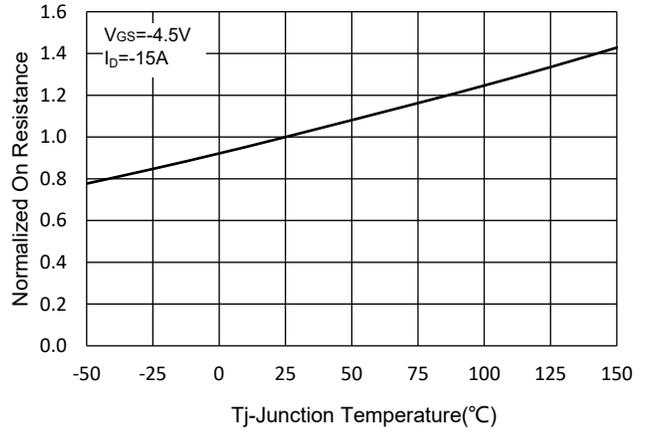


**Curve Characteristics**

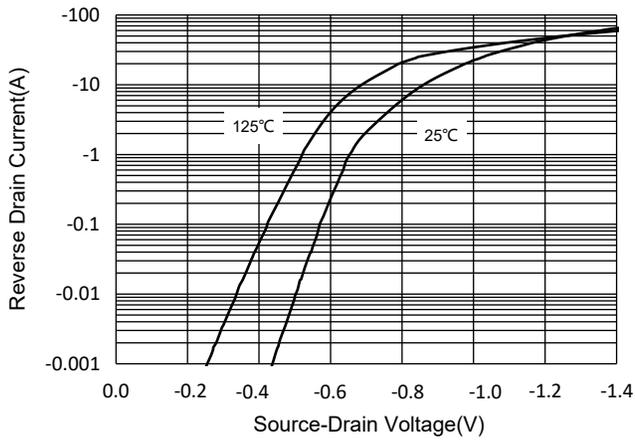
**Fig.7 Normalized Threshold Voltage**



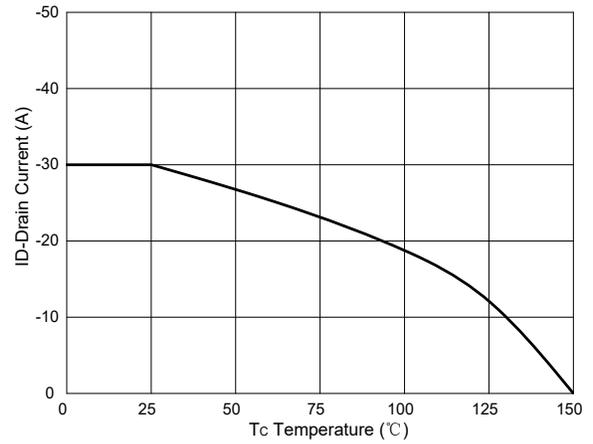
**Fig.8 Normalized On Resistance Characteristics**



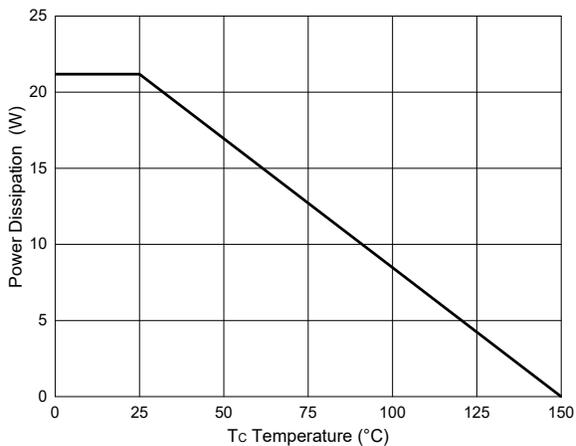
**Fig.9 IS-VSD**



**Fig.10 Drain Current**



**Fig.11 Power Dissipation**



Curve Characteristics

Fig.12 Safe Operation Area

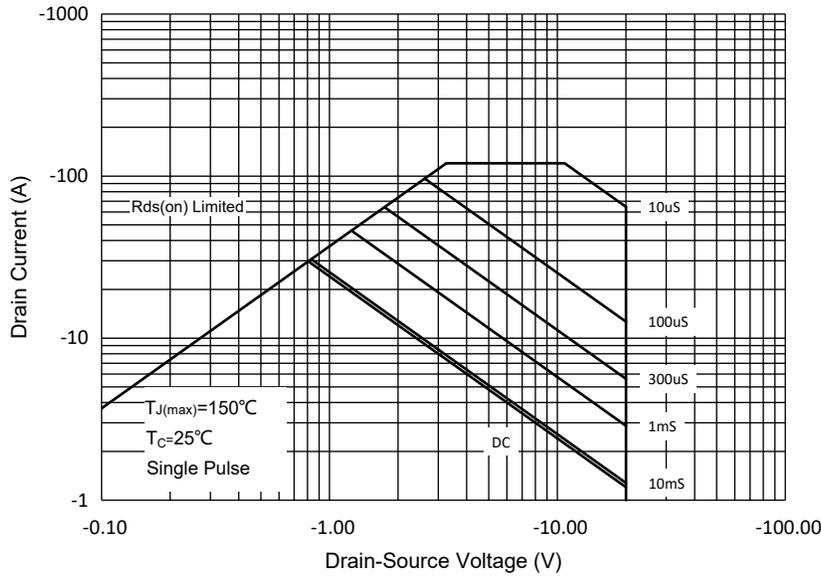
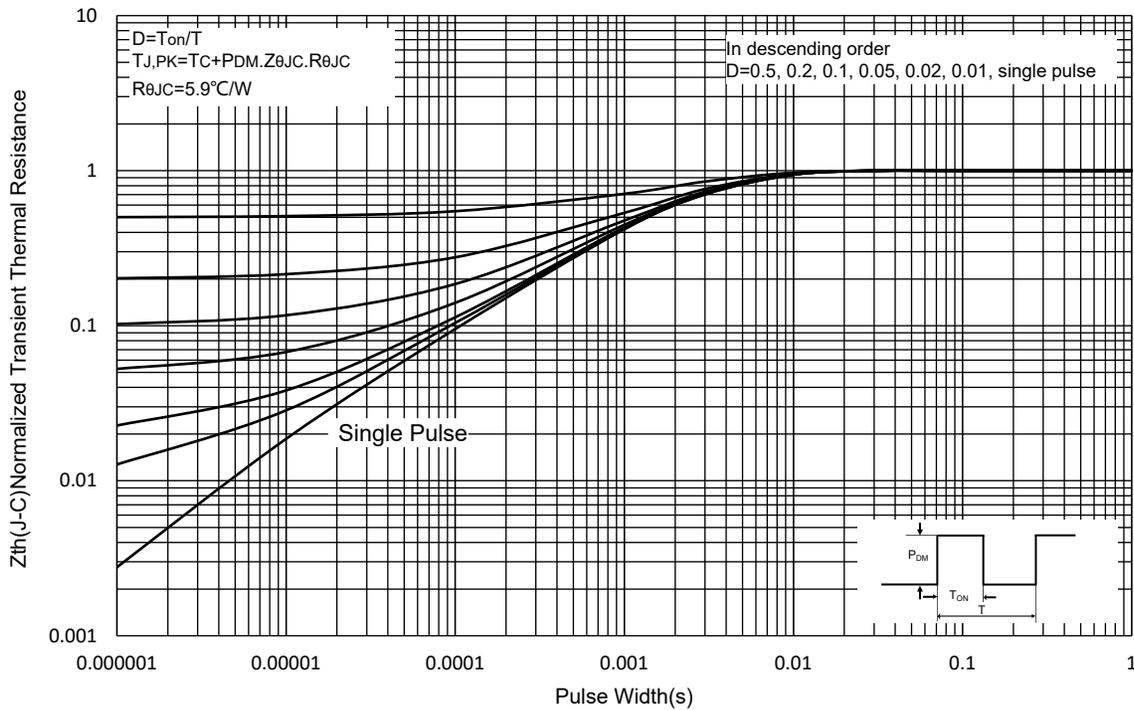


Fig.13 Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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